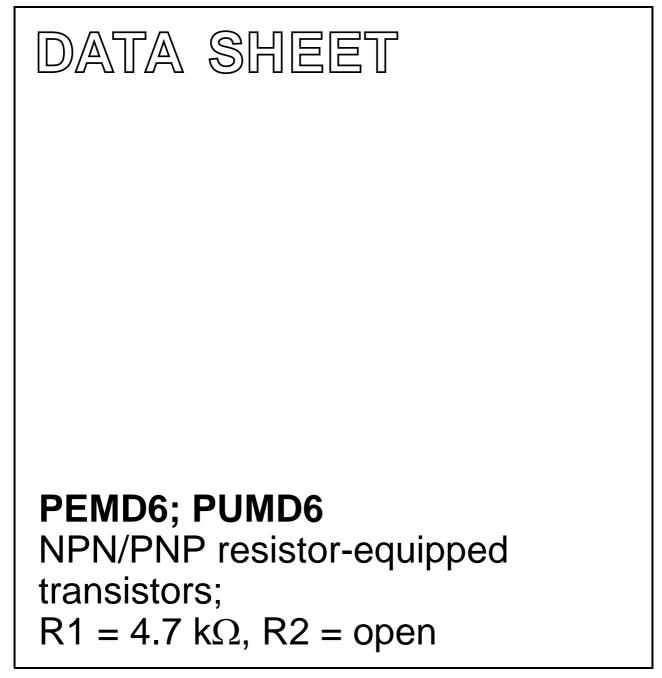
DISCRETE SEMICONDUCTORS



Product data sheet Supersedes data of 2003 Nov 04 2004 Apr 07



PEMD6; PUMD6

FEATURES

- · Built-in bias resistors
- Simplified circuit design
- Reduction of component count
- Reduced pick and place costs.

APPLICATIONS

- Low current peripheral driver
- Replacement of general purpose transistors in digital applications
- Control of IC inputs.

DESCRIPTION

NPN/PNP resistor-equipped transistors (see "_Data_Sheet_Remark Supersedes data of 2003 Nov 04" for package details).

QUICK REFERENCE DATA

SYMBOL	PARAMETER	TYP.	MAX.	UNIT
V _{CEO}	collector-emitter voltage	_	50	V
l _o	output current (DC)	-	100	mA
TR1	NPN	-	-	_
TR2	PNP	-	-	-
R1	bias resistor	4.7	-	kΩ
R2	open	-	-	_

PRODUCT OVERVIEW

TYPE NUMBER	PACKAGE		MARKING CODE	NPN/NPN	PNP/PNP	
	PHILIPS	EIAJ	MARKING CODE	COMPLEMENT	COMPLEMENT	
PEMD6	SOT666	_	D6	PEMH7	PEMB3	
PUMD6	SOT363	SC-88	D*6 ⁽¹⁾	PUMH7	PUMB3	

Note

1. * = p: Made in Hong Kong.

* = t: Made in Malaysia.

SIMPLIFIED OUTLINE, SYMBOL AND PINNING

			PINNING		
TYPE NUMBER	SIMPLIFIED OUTLINE AND SYMBOL	PIN	DESCRIPTION		
PEMD6; PUMD6		1	emitter TR1		
		2	base TR1		
		3	collector TR2		
		4	emitter TR2		
		5	base TR2		
		6	collector TR1		
	1 2 3 Тор view				

Product data sheet

NPN/PNP resistor-equipped transistors; R1 = 4.7 k Ω , R2 = open

PEMD6; PUMD6

ORDERING INFORMATION

TYPE		PACKAGE			
NUMBER NAME		DESCRIPTION	VERSION		
PEMD6	 plastic surface mounted package; 6 leads 		SOT666		
PUMD6	 plastic surface mounted package; 6 leads SO 		SOT363		

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT			
Per transistor;	Per transistor; for the PNP transistor with negative polarity							
V _{CBO}	collector-base voltage	open emitter	-	50	V			
V _{CEO}	collector-emitter voltage	open base	-	50	V			
V _{EBO}	emitter-base voltage	open collector	-	5	V			
I _O	output current (DC)		-	100	mA			
I _{CM}	peak collector current		_	100	mA			
P _{tot}	total power dissipation	$T_{amb} \le 25 \ ^{\circ}C$; note 1						
	SOT363	note 1	-	200	mW			
	SOT666	notes 1 and 2	-	200	mW			
T _{stg}	storage temperature		-65	+150	°C			
Tj	junction temperature		_	150	°C			
T _{amb}	operating ambient temperature		-65	+150	°C			
Per device	·							
P _{tot}	total power dissipation	$T_{amb} \le 25 \ ^{\circ}C$; note 1						
	SOT363	note 1	-	300	mW			
	SOT666	notes 1 and 2	-	300	mW			

Notes

- 1. Transistor mounted on an FR4 printed-circuit board, single-sided copper, standard footprint.
- 2. Reflow soldering is the only recommended soldering method.

PEMD6; PUMD6

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
Per transi	stor	·	· · ·	
R _{th(j-a)}	thermal resistance from junction to ambient	note 1		
	SOT363		625	K/W
	SOT666		625	K/W
Per device	9			
R _{th(j-a)}	thermal resistance from junction to ambient	note 1		
	SOT363		416	K/W
	SOT666		416	K/W

Note

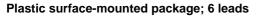
1. Transistor mounted on an FR4 printed-circuit board, single-sided copper, standard footprint.

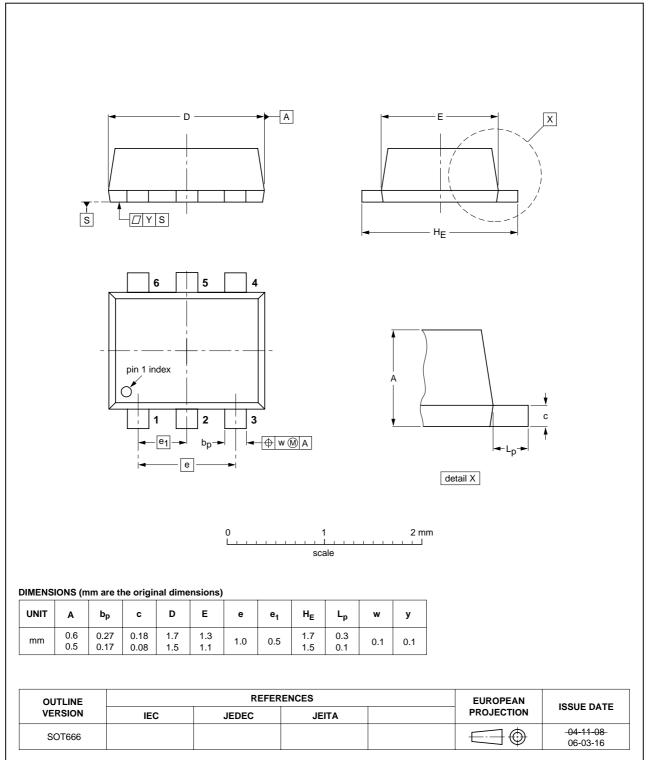
CHARACTERISTICS

 T_{amb} = 25 °C; unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT		
Per transis	Per transistor; for the PNP transistor with negative polarity							
I _{CBO}	collector-base cut-off current	$V_{CB} = 50 \text{ V}; \text{ I}_{E} = 0$	_	_	100	nA		
I _{CEO}	collector-emitter cut-off current	V _{CE} = 30 V; I _B = 0	-	-	1	μA		
		$V_{CE} = 30 \text{ V}; \text{ I}_{B} = 0; \text{ T}_{j} = 150 ^{\circ}\text{C}$	-	-	50	μA		
I _{EBO}	emitter-base cut-off current	$V_{EB} = 5 V; I_{C} = 0$	-	-	100	nA		
h _{FE}	DC current gain	$V_{CE} = 5 \text{ V}; \text{ I}_{C} = 1 \text{ mA}$	200	-	_			
V _{CEsat}	collector-emitter saturation voltage	$I_{C} = 5 \text{ mA}; I_{B} = 0.25 \text{ mA}$	-	-	100	mV		
R1	input resistor		3.3	4.7	6.1	kΩ		
C _c	collector capacitance	$I_E = I_e = 0; V_{CB} = 10 V; f = 1 MHz$						
	TR1 (NPN)		-	_	2.5	pF		
	TR2 (PNP)		-	-	3	pF		

PACKAGE OUTLINES

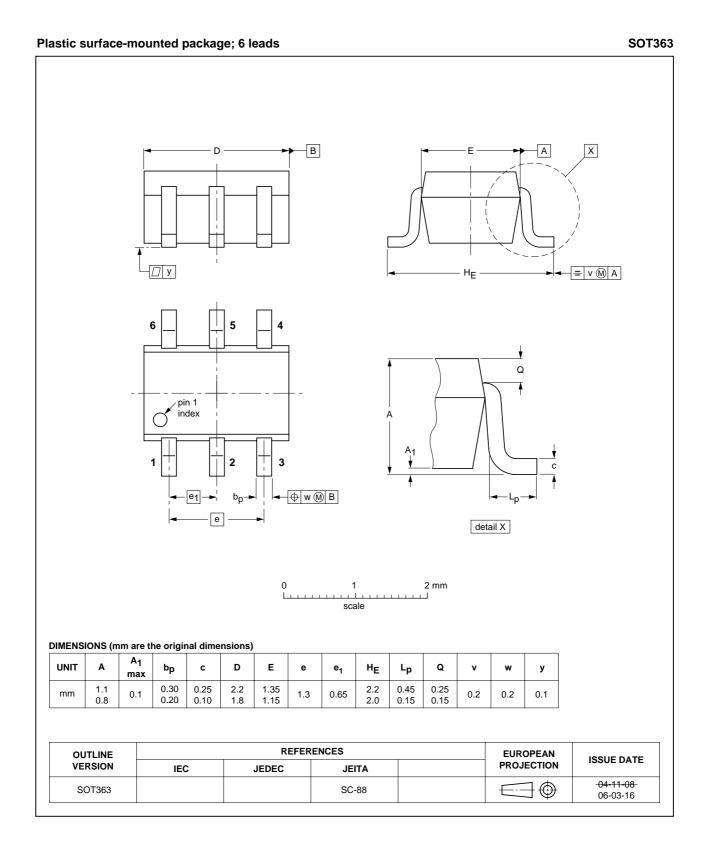




SOT666

PEMD6; PUMD6

PEMD6; PUMD6



PEMD6; PUMD6

DATA SHEET STATUS

DOCUMENT STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

Notes

- 1. Please consult the most recently issued document before initiating or completing a design.
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NXP Semiconductors

Customer notification

This data sheet was changed to reflect the new company name NXP Semiconductors, including new legal definitions and disclaimers. No changes were made to the technical content, except for package outline drawings which were updated to the latest version.

Contact information

For additional information please visit: http://www.nxp.com For sales offices addresses send e-mail to: salesaddresses@nxp.com

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